# <u>MOSFET</u> – Power, Single P-Channel

# -40 V, -140 A, 4.2 m $\Omega$

#### Features

noted) (Notes 1, 2, 3)

Symbol

VDSS

VGS

 $I_D$ 

 $P_D$ 

 $I_D$ 

 $P_D$ 

IDP

T<sub>J</sub>, T<sub>STG</sub>

ls

EAS

T

- Small Footprint (5 x 6 mm) for Compact Design
- Low R<sub>DS(on)</sub> to Minimize Conduction Losses
- NVMFS5A140PLZWF: Wettable Flank Option for Enhanced Optical Inspection

SPECIFICATION MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise

Steadv

Steady

PW  $\leq$  10  $\mu$ s,

duty cycle  $\leq 1\%$ 

State

Operating Junction and Storage Temperature

Single Pulse Drain to Source Avalanche

Lead Temperature for Soldering Purposes

Stresses exceeding those listed in the Maximum Ratings table may damage the

device. If any of these limits are exceeded, device functionality should not be

Energy (L= 1.0 mH,  $I_{L(pk)} = -29 \text{ A}$ )

assumed, damage may occur and reliability may be affected.

Source Current (Body Diode)

(1/8" from case for 10 s)

State

 $T_{\rm C} = 25^{\circ}{\rm C}$ 

 $T_{\rm C} = 25^{\circ}{\rm C}$ 

 $T_A = 25^{\circ}C$ 

 $T_A = 25^{\circ}C$ 

Parameter

• AEC-Q101 Qualified and PPAP Capable

Drain to Source Voltage

Gate to Source Voltage

Continuous Drain,

Power Dissipation

Current R<sub>0JC</sub>,

R<sub>θJC</sub> (Note 1) Continuous Drain:

Current  $R_{\theta JA}$ (Notes 1, 2, 3)

Power Dissipation

R<sub>0JA</sub> (Note 1, 2)

**Pulsed Drain** 

Current

(Notes 1, 3)

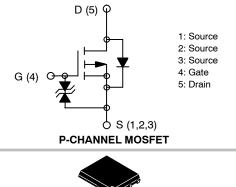
• These Devices are Pb-Free and are RoHS Compliant



# **ON Semiconductor®**

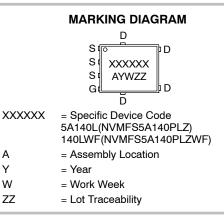
#### www.onsemi.com

V <sub>DSS</sub>	R <sub>DS(ON)</sub> MAX	I <sub>D</sub> MAX
-40 V	4.2 mΩ @ −10 V	–140 A
	7.2 mΩ @ −4.5 V	





(SO-8FL)



#### ORDERING INFORMATION See detailed ordering and shipping information on page 7 of

this data sheet

THERMAL CHARACTERISTICS

 $\begin{tabular}{|c|c|c|c|c|} \hline Symbol & Parameter & Value & Unit \\ \hline $R_{\theta JC}$ & Junction to Case Steady State \\ \hline $R_{\theta JA}$ & Junction to Ambient Steady State (Note 2) & 39 \\ \hline \end{tabular}$ 

Value

-40

±20

-140

200

-20

3.8

-560

–55 to

+175

-140

420

260

Unit

V

v

А

W

А

W

А

°C

А

mJ

°C

 The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

2. Surface mounted on FR4 board using a 650  $\rm mm^2,$  2 oz. Cu pad.

3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

#### **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Тур	Max	Unit
OFF CHARA	CTERISTICS						
V <sub>(BR)DSS</sub>	Drain to Source Breakdown Voltage	$I_{\rm D}$ = -1 mA, $V_{\rm GS}$ = 0 V		-40			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS}$ = -40 V, $V_{GS}$ = 0 V	$T_J = 25^{\circ}C$			-1.0	μA
			T <sub>J</sub> = 100°C (Note 4)			-100	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS}$ = ±16 V, $V_{DS}$ = 0 V				±10	μA

#### **ON CHARACTERISTICS** (Note 5)

V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ mA}$		-1.2		-2.6	V
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -50 A		3.2	4.2	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -50 A		5.0	7.2	mΩ
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -50 \text{ A}$			125		S

#### **CHARGES, CAPACITANCES & GATE RESISTANCE**

C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0 V, f = 1 MHz	7400	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -20 V,	1030	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		720	
Q <sub>g(tot)</sub>	Total Gate Charge	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -50 \text{ A}$	136	
Q <sub>gs</sub>	Gate to Source Charge	V <sub>DS</sub> = -20 V,	26	nC
Q <sub>gd</sub>	Gate to Drain Charge	]	31	

#### SWITCHING CHARACTERISTICS (Note 6)

t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DS} = -20 \text{ V}, \text{ I}_{D} = -50 \text{ A},$		50	
t <sub>r</sub>	Rise Time	$V_{GS}$ = -10 V, $R_{G}$ = 50 $\Omega$		860	
t <sub>d(off)</sub>	Turn-Off Delay Time			540	ns
t <sub>f</sub>	Fall Time			740	

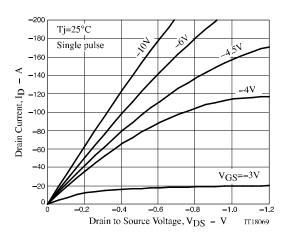
#### DRAIN-SOURCE DIODE CHARACTERISTICS

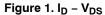
	$V_{SD}$	Forward Diode Voltage	$V_{GS} = 0 V, I_{S} = -50 A$		-0.83	-1.5	V
	t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 V, I_{S} = -50 A$		108		ns
Ī	Q <sub>rr</sub>	Reverse Recovery Charge	di/dt = 100 A/µs		236		nC

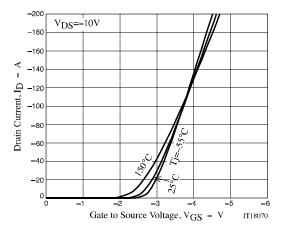
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. The maximum value is specified by design at  $T_J = 100$  °C. Product is not tested to this condition in production. 5. Pulse Test: pulse width  $\leq 300 \ \mu$ s, duty cycle  $\leq 2 \ \%$ .

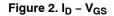
6. Switching characteristics are independent of operating junction temperatures.

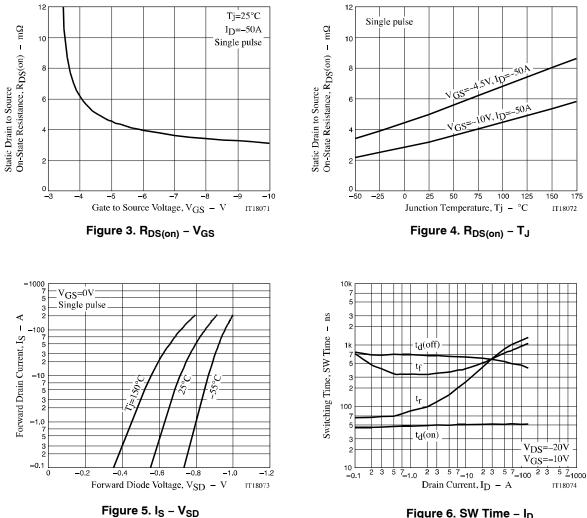
### **TYPICAL CHARACTERISTICS**







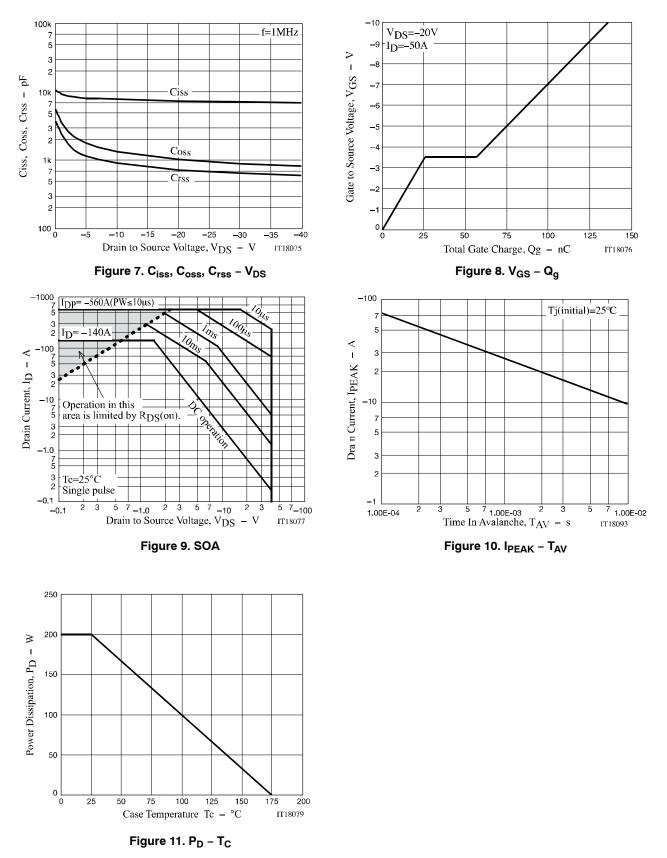








### **TYPICAL CHARACTERISTICS**



## **TYPICAL CHARACTERISTICS**

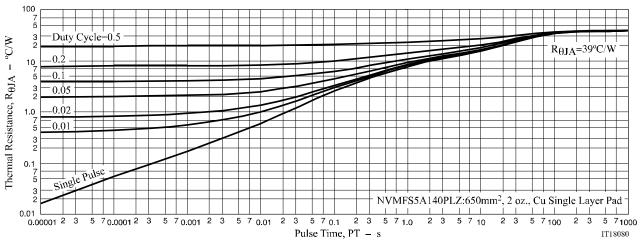


Figure 12.  $R_{\theta JA}$  – Pulse Time

#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping (Qty / Packing) $^{\dagger}$
NVMFS5A140PLZT1G	5A140L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	1.500 / Tape & Reel
NVMFS5A140PLZWFT1G	140LWF	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free / Wettable Flanks)	1.500 / Tape & Reel
NVMFS5A140PLZT3G	5A140L	DFN5 5x6, 1.27P (SO-8FL) (Pb-Free)	5.000 / Tape & Reel
NVMFS5A140PLZWFT3G	140LWF	DFN5 5x6, 1.27P (SO–8FL) (Pb-Free / Wettable Flanks)	5.000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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